NPN Medium Power Transistor (Switching)

UMT2222A/SST2222A/MMST2222A/RXT2222A/PN2222A

Features

- 1) BVcEo<40V (Ic=10mA)
- 2) Complements the UMT2907A/SST2907A/MMST2907A /RXT2907A/PN2907A.

Package, marking and packaging specifications

Туре	UMT2222A	SST2222A	MMST2222A	RXT2222A	PN2222A
Package	UMT3	SST3	SMT3	MPT3	TO-92
Marking	R1P	R1P	R1P	CB *	_
Code	T106	T116	T146	T100	T93
Basic ordering unit (pieces)	3000	3000	3000	1000	3000

Indicates lot number.

●Absolute maximum ratings (Ta=25℃)

P	Symbol	Limits	Unit		
Collector-base voltage		Vcao	75	٧	
Collector-emitter voltage		VCEO	40	v	
Emitter-base vol	tage	VEBO	6	v	
Collector current		lc	0.6	A	
Collector power dissipation	UMT2222A,SST2222AV, MMST2222A		0.2		
	SST2222A	Pc	0.35	w ,	
	RXT2222A		0.5		
	PN2222A		0.625		
Junction temper	ature	Tj	150	Ċ	
Storage tempera	iture	Tstg	-55~150	r	

* On 7 x 5 x 0.6 mm ceramic board



●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Тур.	Max.	Ųnit	Conditions
Collector-base breakdown voltage	BVcso	75	—	-	V	Ic=10 µA
Collector-emitter breakdown voltage	BVCEO	40		- 1	v	Ic=10mA
Emitter-base breakdown voltage	Βνεθο	6		—	V	I∈=10 µ A
Collector cutoff current	Icao	-	-	100	nA	Vcs=60V
Emitter cutoff current	lebo	-	-	100	nA	VEB=3V
Collector-emitter saturation voltage	VCE(eat)	-	- 1	0.3	v	Ic/Is=150mA/15mA
		_		1		lc/ls=500mA/50mA
Base-emitter saturation voltage	VBE(sat)	0.6	_	1.2	v	Ic/is=150mA/15mA
		_	- 1	2		Ic/Is=500mA/50mA
DC current transfer ratio	hre	35	_	_	- -	Vc=10V, lc=0.1mA
		50	_	_		Vce=10V, lc=1mA
		75	_			Vce=10V, Ic=10mA
		50	-			VcE=1V, lc=150mA
		100	-	300		Vc=10V , lc=150mA
		40				Vc=10V, lc=500mA
Transition frequency	fτ	300	—		MHz	Vcc=20V, lc=-20mA, f=100MHz
Output capacitance	Cob		-	8	pF	Vcs=10V, f=100kHz
Emitter input capacitance	Cib	-	_	25	pF	VEB=0.5V , f=100kHz
Delay time	td			10	ns	Vcc=30V, Vse(oFF)=0.5V, Ic=150mA, Is1=15mA
Rise time	tr		_	25	ns	Vcc=30V, Vse(OFF)=0.5V, Ic=150mA, Is1=15mA
Storage time	tstg	-	_	225	ns	Vcc=30V, lc=150mA, ls1=-la2=15mA
Fall time	tt		_	60	ns	Vcc=30V, lc=150mA, ls1=-ls2=15mA

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(SPEC-C31)

Electrical characteristic curves





Fig.3 DC current gain vs. collector current (I)



Fig.2 Collector-emitter saturation voltage vs. collector current



Fig.4 DC current gain vs. collector current (II)



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Electrical characteristic curves



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10

current

100

Rise time vs. collector

Ta=25℃

Vcc=30V

1000

vs. voltage

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.



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Types and features of surface-mount packages

Packages



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Packages

EXPLANATION

Types and features of leaded packages



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Packages



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Packages

Туре	External dimensions (Units : mm)	Features
TO-220FN	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	The TO-220FN features the same performance as the TO- 220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short- circuiting problems with neighboring components and the chassis. To make the heigth to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.

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